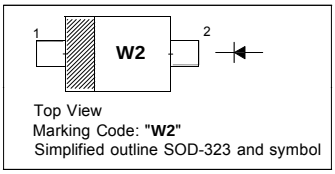
Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



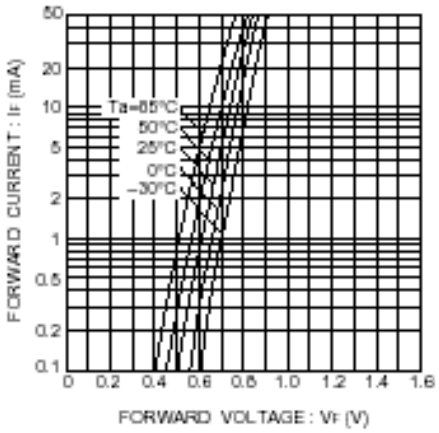
Top View
Marking Code: "**W2**"
Simplified outline SOD-323 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

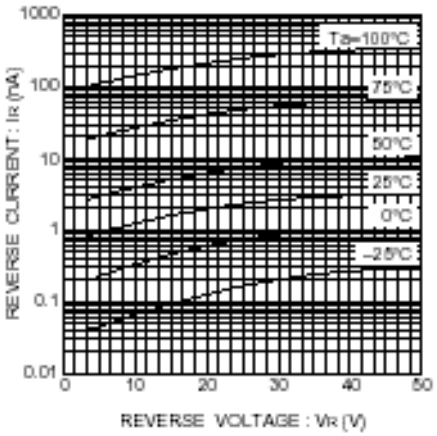
Parameter		Symbol	Value	Unit
Repetitive Peak Reverse Voltage		V_{RRM}	85	V
Reverse Voltage		V_R	75	V
Continuous Forward Current		I_F	125	mA
Repetitive Peak Forward Current		I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	at t = 1 s at t = 1 ms at t = 1 µs	I_{FSM}	0.5 1 4	A
Power Dissipation		P_{tot}	250	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	- 65 to + 150	°C

Characteristics at T_a = 25 °C

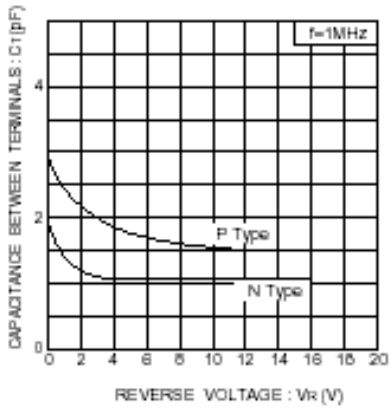
Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 1 mA at I_F = 10 mA at I_F = 50 mA at I_F = 150 mA	V_F	 715 855 1 1.25	 mV mV V V
Reverse Current at V_R = 25 V at V_R = 75 V at V_R = 25 V, T_j = 150 °C at V_R = 75 V, T_j = 150 °C	I_R	 30 1 30 50	 nA µA µA µA
Diode Capacitance at V_R = 0, f = 1 MHz	C_d	2	pF
Reverse Recovery Time at I_F = 10 mA, I_R = 10 mA, R_L = 100 Ω	t_{rr}	4	ns



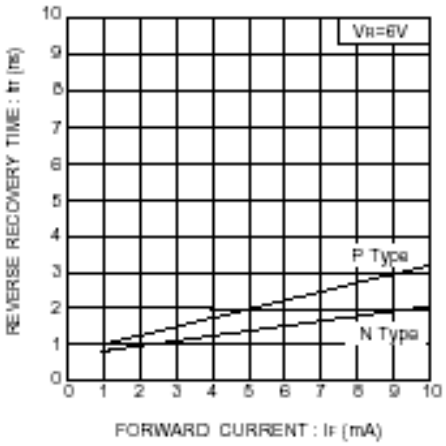
Forward characteristics



Reverse characteristics



Capacitance between terminals characteristics



Reverse recovery time